

STGD10NC60H

N-channel 10A - 600V - DPAK Very fast PowerMESH™ IGBT

Features

Туре	V _{CES}	V _{CE(sat)} (Max)@ 25°C	l _C @100°C
STGD10NC60H	600V	< 2.5V	10A

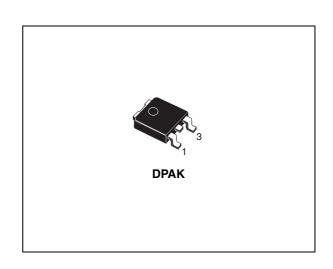
- Low on-voltage drop (V_{cesat})
- Low C_{RES} / C_{IES} ratio (no cross-conduction susceptibility)

Description

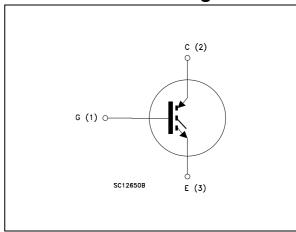
Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH[™] IGBTs, with outstanding performances. The suffix "H" identifies a family optimized for high frequency applications in order to achieve very high switching performances (reduced tfall) manta in ing a low voltage drop.

Applications

- High frequency motor controls
- SMPS and PFC in both hard switch and resonant topologies
- Motor drivers



Internal schematic diagram



Order code

Part number	Marking	Package	Packaging
STGD10NC60H	GD10NC60H	DPAK	Tape & reel

Contents STGD10NC60H

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STGD10NC60H Electrical ratings

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{GS} = 0)	600	V
I _C ⁽¹⁾	Collector current (continuous) at T _C = 25°C	20	Α
I _C ⁽¹⁾	Collector current (continuous) at T _C = 100°C	10	Α
I _{CL} ⁽²⁾	Collector current (pulsed)	40	Α
V _{GE}	Gate-emitter voltage	±20	V
P _{TOT}	Total dissipation at T _C = 25°C	60	W
T _j	Operating junction temperature	- 55 to 150	°C

^{1.} Calculated according to the iterative formula:

$$I_{C}(T_{C}) = \frac{T_{JMAX}^{-T}C}{R_{THJ-C}^{\times V}CESAT(MAX)^{(T_{C}, \ I_{C})}}$$

2. V_{clamp} =480V, Tj=150°C, R_G =10 Ω , V_{GE} =15V

Table 2. Thermal resistance

Symbol	Parameter	Value	Unit
Rthj-case	Thermal resistance junction-case max	2.08	°C/W
Rthj-amb	Thermal resistance junction-ambient max	62.5	°C/W

Electrical characteristics STGD10NC60H

2 Electrical characteristics

 $(T_{CASE}=25^{\circ}C \text{ unless otherwise specified})$

Table 3. Static

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{BR(CES)}	Collector-emitter breakdown voltage	I _C = 1mA, V _{GE} = 0	600			٧
I _{CES}	Collector cut-off current (V _{GE} = 0)	V_{CE} = Max rating, T_{C} = 25°C V_{CE} =Max rating, T_{C} = 125°C			150 1	μA mA
I _{GES}	Gate-emitter leakage current (V _{CE} = 0)	V _{GE} = ±20V, V _{CE} = 0			±100	nA
V _{GE(th)}	Gate threshold voltage	$V_{CE} = V_{GE}, I_{C} = 250 \mu A$	3.75		5.75	V
V _{CE(sat)}	Collector-emitter saturation voltage	V _{GE} = 15V, I _C = 5A V _{GE} = 15V, I _C = 5A, Tc= 125°C		1.9 1.7	2.5	V V
9 _{fs}	Forward transconductance	V _{CE} = 15V _, I _C = 5A		3.5		S

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C _{ies} C _{oes} C _{res}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{CE} = 25V, f = 1MHz,$ $V_{GE} = 0$		365 43 8.3		pF pF pF
Q _g Q _{ge} Q _{gc}	Total gate charge Gate-emitter charge Gate-collector charge	$V_{CE} = 390V$, $I_{C} = 5A$, $V_{GE} = 15V$, (see Figure 16)		19.2 4.5 7		nC nC nC

Table 5. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)} t _r (di/dt) _{on}	Turn-on delay time Current rise time Turn-on current slope	V_{CC} = 390V, I_{C} = 5A R_{G} = 10 Ω V_{GE} = 15V, Figure 15. Figure 17.		14.2 5 1000		ns ns A/µs
t _{d(on)} t _r (di/dt) _{on}	Turn-on delay time Current rise time Turn-on current slope	V_{CC} = 390V, I_{C} = 5A R_{G} = 10 Ω V_{GE} = 15V, T_{j} = 125°C Figure 15. Figure 17.		14 5 920		ns ns A/µs
t _r (V _{off}) t _d (_{off}) t _f	Off voltage rise time Turn-off delay time Current fall time	V_{cc} = 390V, I_{C} = 5A, R_{GE} = 10 Ω , V_{GE} = 15V, Figure 15. Figure 17.		27 72 85		ns ns ns
t _r (V _{off}) t _d (_{off}) t _f	Off voltage rise time Turn-off delay time Current fall time	V_{cc} = 390V, I_{C} = 5A, R_{GE} =10 Ω , V_{GE} =15V, T_{j} =125°C Figure 15. Figure 17.		50 108 139		ns ns ns

Table 6. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
E _{on} E _{off} ⁽¹⁾ E _{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	V_{CC} = 390V, I_{C} = 5A R_{G} = 10 Ω V_{GE} =15V, Tj=25°C (see Figure 17)		31.8 95 126.8		μJ μJ μJ
E _{on} E _{off} ⁽¹⁾ E _{ts}	Turn-on switching losses Turn-off switching Losses Total switching losses	V_{CC} = 390V, I_{C} = 5A R_{G} = 10 Ω , V_{GE} = 15V, T_{J} = 125°C (see Figure 17)		61.8 173 234.8		μJ μJ μJ

^{1.} Turn-off losses include also the tail of the collector current

Electrical characteristics STGD10NC60H

2.1 Electrical characteristics (curves)

Figure 1. Output characteristics

Figure 2. Transfer characteristics

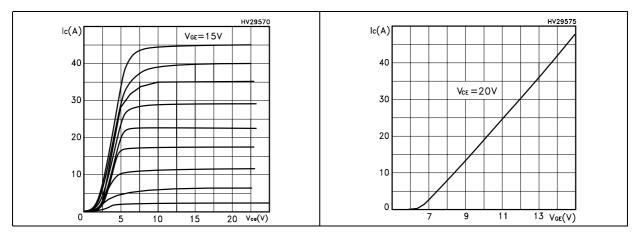


Figure 3. Transconductance

Figure 4. Collector-emitter on voltage vs temperature

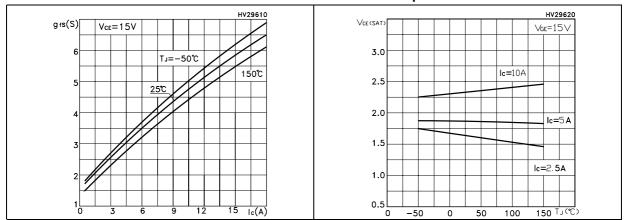


Figure 5. Gate charge vs gate-source voltage Figure 6. Capacitance variations

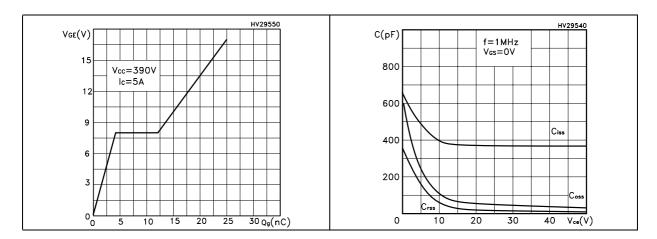


Figure 7. Normalized gate threshold voltage Figure 8. Collector-emitter on voltage vs vs temperature collector current

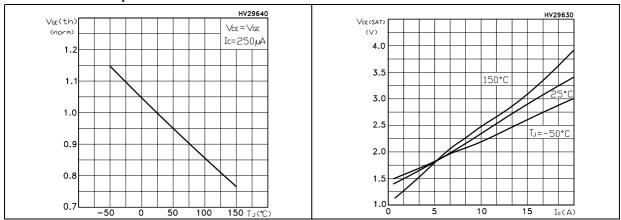


Figure 9. Normalized breakdown voltage vs Figure 10. Switching losses vs temperature temperature

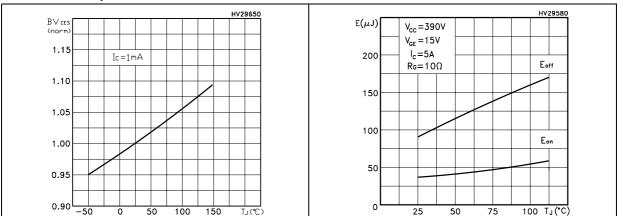
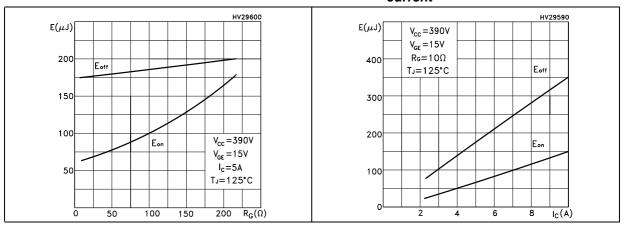


Figure 11. Switching losses vs gate resistance Figure 12. Switching losses vs collector current

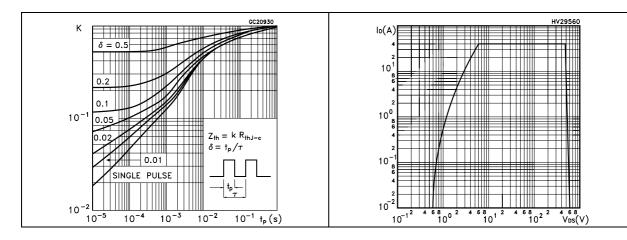


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Figure 13. Thermal Impedance

Figure 14. Turn-off SOA



STGD10NC60H Test circuits

3 Test circuits

Figure 15. Test circuit for inductive load switching

Figure 16. Gate charge test circuit

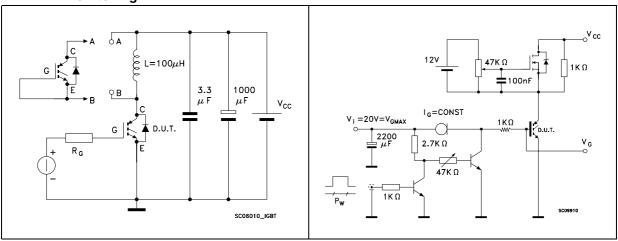
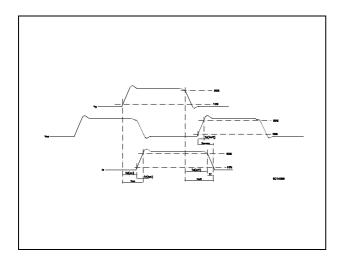


Figure 17. Switching waveform

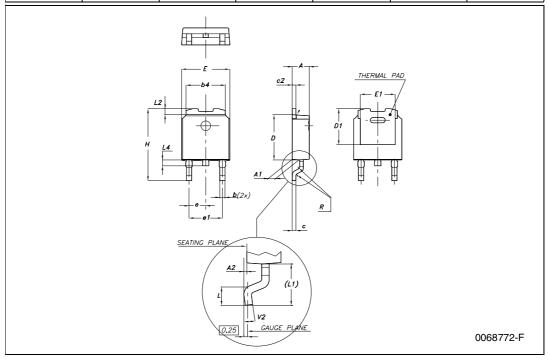


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

DPAK MECHANICAL DATA

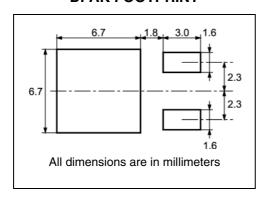
DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
В	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
С	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
Е	6.4		6.6	0.252		0.260
E1		4.7			0.185	
е		2.28			0.090	
e1	4.4		4.6	0.173		0.181
Н	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°



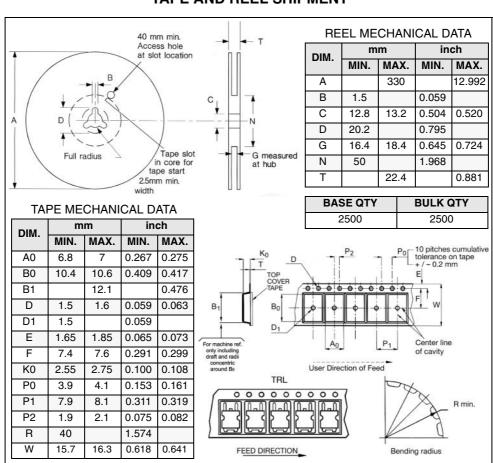
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5 Packaging mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT



STGD10NC60H Revision history

6 Revision history

Table 7. Revision history

Date	Revision	Changes
02-Apr-2007	1	Initial release.

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